

**IN THE SPECIFICATION:**

**Replace the paragraph at page 23, line 20, with the following rewritten paragraph:**

A1 Next, the amorphous silicon film 18 is formed in a 10 nm-thick on the polycrystalline silicon film 16 by, e.g., CVD method (FIG. 6D). At this time, a native oxide film 17 is formed between the polycrystalline silicon film 16 and the amorphous silicon film 18.

**Replace the paragraph at page 29, line 5, with the following rewritten paragraph:**

A2  
A.M.  
12/09/02  
Next, a 10 nm-thick amorphous silicon film 18 is formed on the polycrystalline silicon film 40 by, e.g., CVD method (FIG. 11A). At this time, a native oxide film 17 is present between the polycrystalline silicon film 40 and the amorphous silicon film 18.

**IN THE CLAIMS:**

**AMEND** claims 1 and 2 as follows:

- Sub  
/C1  
A3
1. (Amended) A semiconductor device comprising:  
a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and  
a gate electrode formed above the silicon substrate between the pair of impurity diffused regions  
with a gate insulation film interposed therebetween, the gate electrode being formed of a first polycrystalline silicon film formed on the gate insulation film, a second polycrystalline silicon film formed on the first polycrystalline silicon film having a thickness thinner than that of the first polycrystalline silicon film and